

# Electronics Lab 2: Diodes

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In this lab, the V-I curves for germanium and silicon diodes were measured using a voltage/current divider.

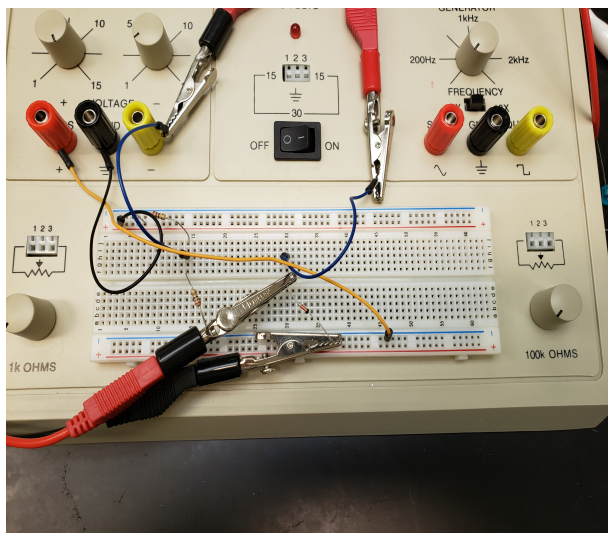


FIG. 1. The diode circuit

## I. INTRODUCTION

The purpose of this laboratory is to study Kirchhoff's Laws. This will be done by constructing voltage dividers, and then a current divider, and seeing how the two circuits conform to Kirchhoff's Laws. Using these circuits, we carefully map the V-I curve of a silicon diode and a germanium diode.

## II. THEORETICAL MODEL

As we know from lab one, we expect the diodes to be non-ohmic, rather we will fit them to the curve:

$$I = I_0(e^{eV/nk_B T} - 1) \quad (1)$$

Where  $n$  is a quality factor, and  $e, k_B, T, V$  are the charge of an electron, Boltzmann constant, temperature, and voltage respectively.

## III. EXPERIMENT

For this experiment first we played around with understanding current and voltage dividers. Then, once we understood how to use and create these, we chose a circuit and took data for both diodes.

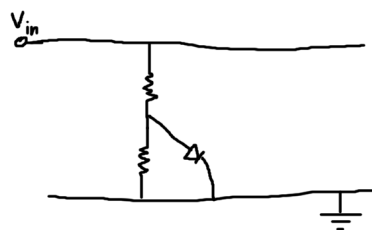


FIG. 2. An example of a simple voltage divider w/ diode

### A. Procedure

First, we created the dividers, and understood how to create them. Next, we chose a circuit and took data backwards and forwards for each of the diodes. For the diodes, resistors of 270 ohms were used to divide.

### B. Data

The graph, fit, and tables for each diode is included below.

## IV. CONCLUSION

Both diodes followed the expected theoretical models closely, with an  $R^2$  value of .9997 and .9282 for the silicon and germanium diodes respectively.

## ACKNOWLEDGEMENTS

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	Data Set	
	X	Y
1	0.488	0.13
2	0.525	0.3
3	0.566	0.74
4	0.6	1.8
5	0.645	3.83
6	0.664	5.63
7	0.686	9.07
8	0.702	13.05
9	0.712	16.35
10	0.718	18.4
11	0.72	19.26
12	0.723	20.7
13	0.727	22.06
14	-0.434	-0.00004
15	-0.629	0.000057
16	-0.932	0.000084
17	-1.186	0.000108
18	-1.377	0.000126
19	-1.634	0.000148
20	-1.734	0.000162
21	0.73	25.306
22	0.736	27.916
23	0.74	30.786
24	0.743	32.908
25	0.452	0.045

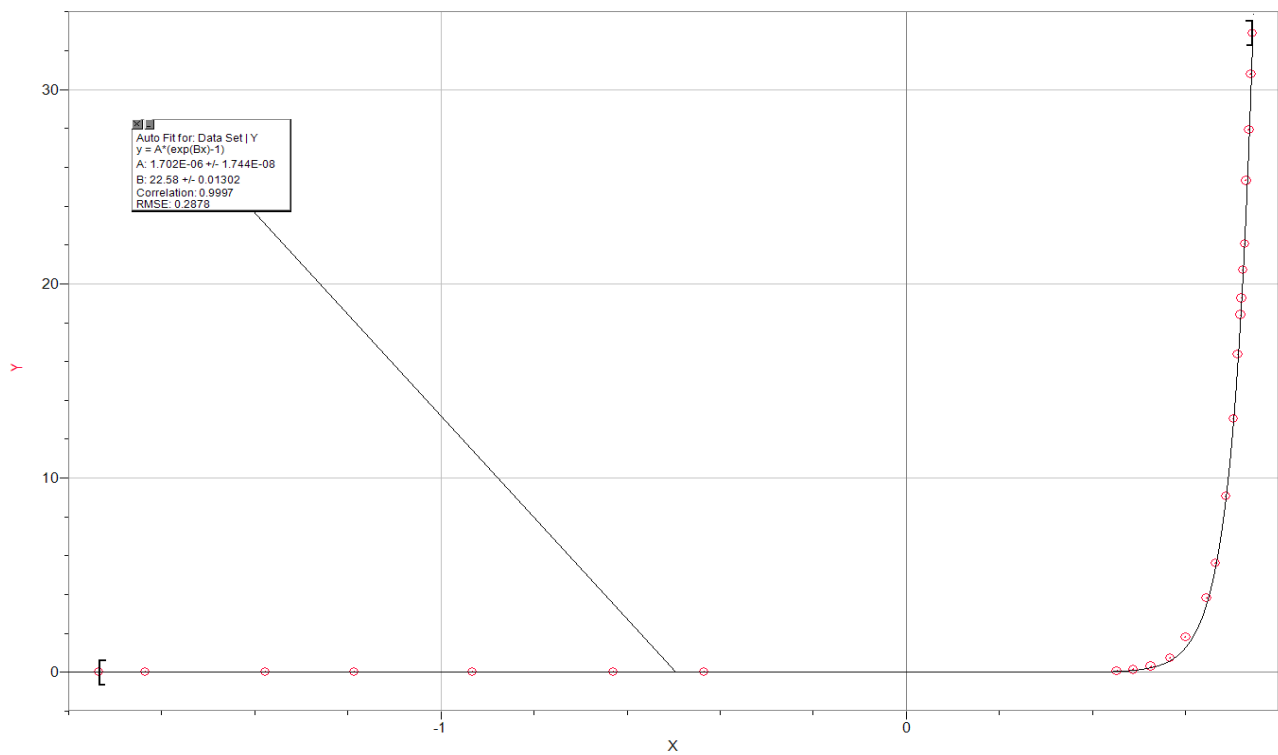


FIG. 3. The Silicon Diode Table and Graph

	Data Set	
	X	Y
1	0.313	1.098
2	0.371	2.912
3	0.431	5.443
4	0.477	7.718
5	0.512	9.477
6	0.554	11.675
7	0.619	15.342
8	0.677	20.258
9	0.708	25.357
10	0.698	23.506
11	0.719	27.622
12	0.733	31.588
13	0.736	32.666
14	-0.37	0.000052
15	-0.49	0.000063
16	-0.568	-0.00007
17	-0.071	0.000084
18	-0.88	-0.0001
19	-1.063	0.000117
20	-1.213	0.000131
21	-1.462	0.000155
22	-1.569	0.000164

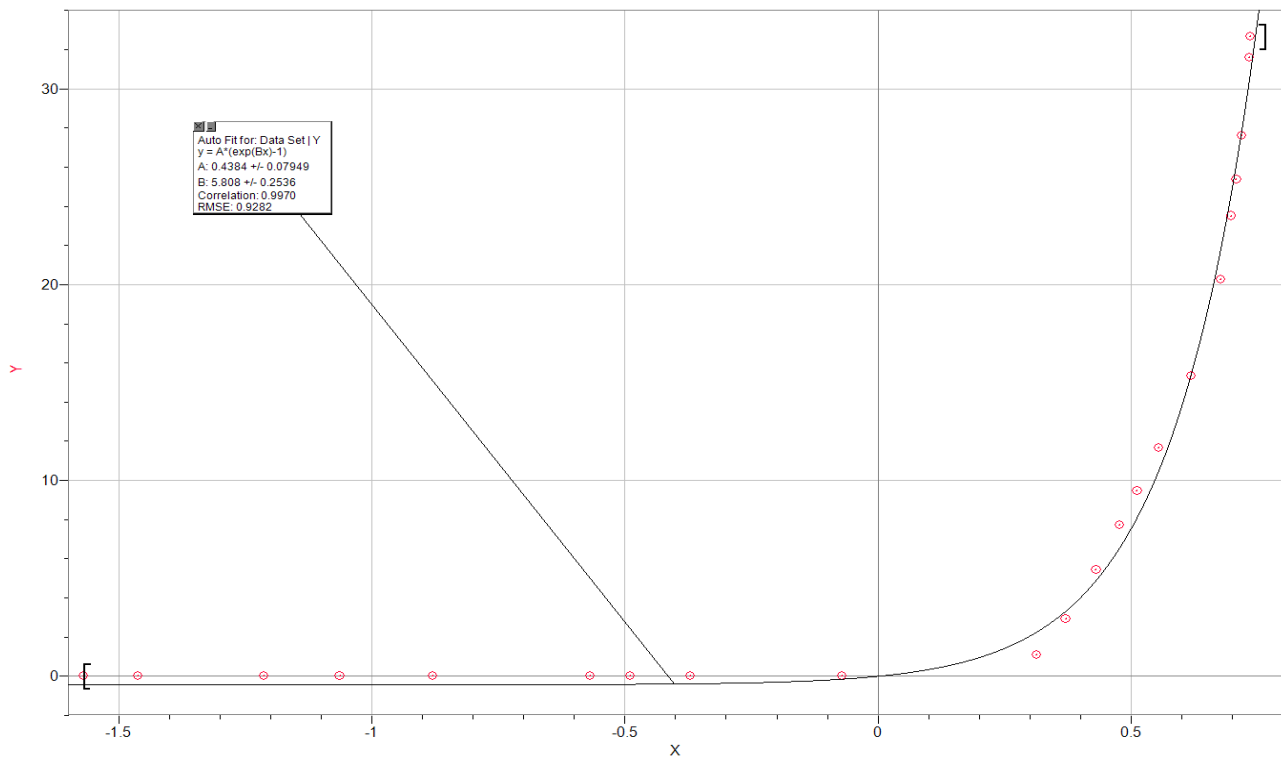


FIG. 4. The Germanium Diode Table and Graph

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